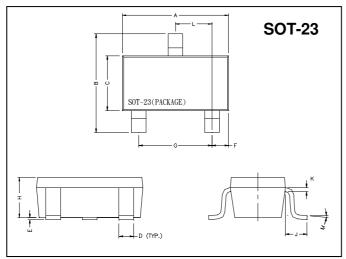
G401SD

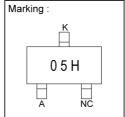
SURFACE MOUNT, SCHOTTKY BARRIER DIODE **VOLTAGE 30V, CURRENT 0.2A**

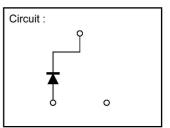
Description

The G401SD is high frequency rectification for switching power supply.

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.	NEF.	Min.	Max.
Α	2.70	3.10	G	1.90 REF.	
В	2.40	2.80	Н	1.00	1.30
С	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
Е	0	0.10	L	0.85	1.15
F	0.45	0.55	М	0°	10°

Absolute Maximum Ratings at TA = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj.	+125	$^{\circ}\mathbb{C}$
Storage Temperature	Tstg -55 ~ +125		$^{\circ}\mathbb{C}$
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	30	V
Maximum RMS Voltage	V _{RMS}	21	V
Maximum DC Blocking Voltage	V_{DC}	30	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3.0	Α
Typical Junction Capacitance between Terminal (Note 1)	CJ	40	pF
Maximum Average Forward Rectified Current	lo	0.2	A
Total Power Dissipation	PD	225	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

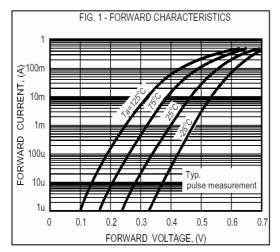
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)R	30	-	-	٧	IR=100μA
Maximum Instantaneous Forward Voltage	VF	-	-	500	mV	IF=200mA
Maximum Average Reverse Current	lR	-	-	50	μΑ	VR1=10V
iviaximum Average neverse Current		-	-	100	μΑ	VR2=30V

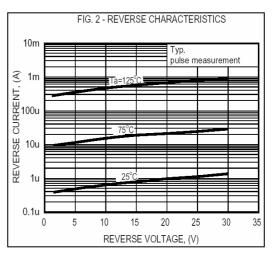
Notes: 1. Measured at 1.0 MHz and 0 reverse bias voltage.

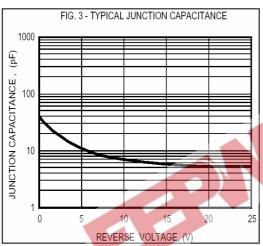
2. ESD sensitive product handling required.

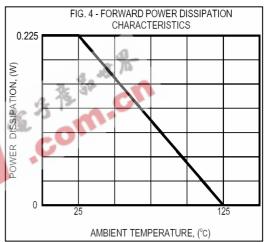
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Characteristics Curve









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